



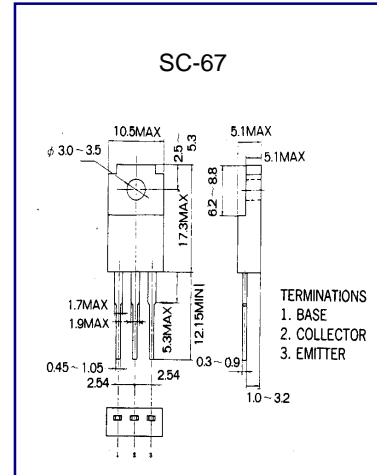
2SC5416LS

NPN SILICON TRANSISTOR

**HIGH VOLTAGE POWER
SWITCHING APPLICATIONS**

ABSOLUTE MAXIMUM RATINGS(T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	V _{CE0}	1000	V
Collector-Emitter Voltage	V _{CEO}	450	V
Emitter-Base Voltage	V _{EB0}	9	V
Collector Current (DC)	I _C	4	A
Collector Current (Pulse)	I _C	8	A
Base Current (DC)	I _B	2	A
Base Current (Pulse)	I _B	4	A
Collector Dissipation (T _c =25°C)	P _C	100	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-65~150	°C



ELECTRICAL CHARACTERISTICS (T_A=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Emitter Sustaining Voltage	V _{CE0(SUS)}	I _C =100mA, I _B =0	450			V
Collector Cutoff Current	I _{CES}	V _{CE} =850V, V _{EB} =0			1	mA
Emitter Cutoff Current	I _{EB0}	V _{CE} =1000V, V _{EB} =0			1	mA
DC Current Gain	h _{FE}	V _{EB} =9V, I _C =0	30		10	μA
Collector Emitter Saturation Voltage	V _{CE(sat)}	I _C =0.1A, V _{CE} =5V			50	V
Fall Time	t _f	I _C =2.5A, I _B =0.5A			1.5	μS
					0.15	μS